



High power cycling capability
Low on-state and switching losses
Optimized for line frequency rectifiers
Designed for traction and industrial applications

Rectifier Diode
Type D143-630-40

Average forward current				I _{FAV}	630 A				
Repetitive peak reverse voltage				V _{RRM}	2400...4000 V				
V _{RRM} , V	2400	2600	2800	3000	3200	3400	3600	3800	4000
Voltage code	24	26	28	30	32	34	36	38	40
T _j , °C				−60...+150					

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters			Units	Values		Test conditions				
ON-STATE										
I _{FAV}	Maximum allowable average forward current			A	630 840	T _c =117 °C; Double side cooled; T _c =100 °C; Double side cooled; 180° half-sine wave; 50 Hz				
I _{FRMS}	RMS forward current			A	989	T _c =117 °C; Double side cooled; 180° half-sine wave; 50 Hz				
I _{FSM}	Surge forward current			kA	14.5 17.0	T _j =T _j max T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V			
					15.0 17.0	T _j =T _j max T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V			
I ² t	Safety factor			A ² s·10 ³	1050 1440	T _j =T _j max T _j =25 °C	180° half-sine wave; t _p =10 ms; single pulse; V _R =0 V			
					930 1190	T _j =T _j max T _j =25 °C	180° half-sine wave; t _p =8.3 ms; single pulse; V _R =0 V			
BLOCKING										
V _{RRM}	Repetitive peak reverse voltages			V	2400...4000	T _{j min} < T _j <T _{j max} ; 180° half-sine wave; 50 Hz				
V _{RSM}	Non-repetitive peak reverse voltages			V	2500...4100	T _{j min} < T _j <T _{j max} ; 180° half-sine wave; single pulse				
V _R	Reverse continuous voltages			V	0.6V _{RRM}	T _j =T _j max				
THERMAL										
T _{stg}	Storage temperature			°C	−60...+50					
T _j	Operating junction temperature			°C	−60...+150					
MECHANICAL										
F	Mounting force			kN	14.0...16.0					
a	Acceleration			m/s ²	50	Device clamped				

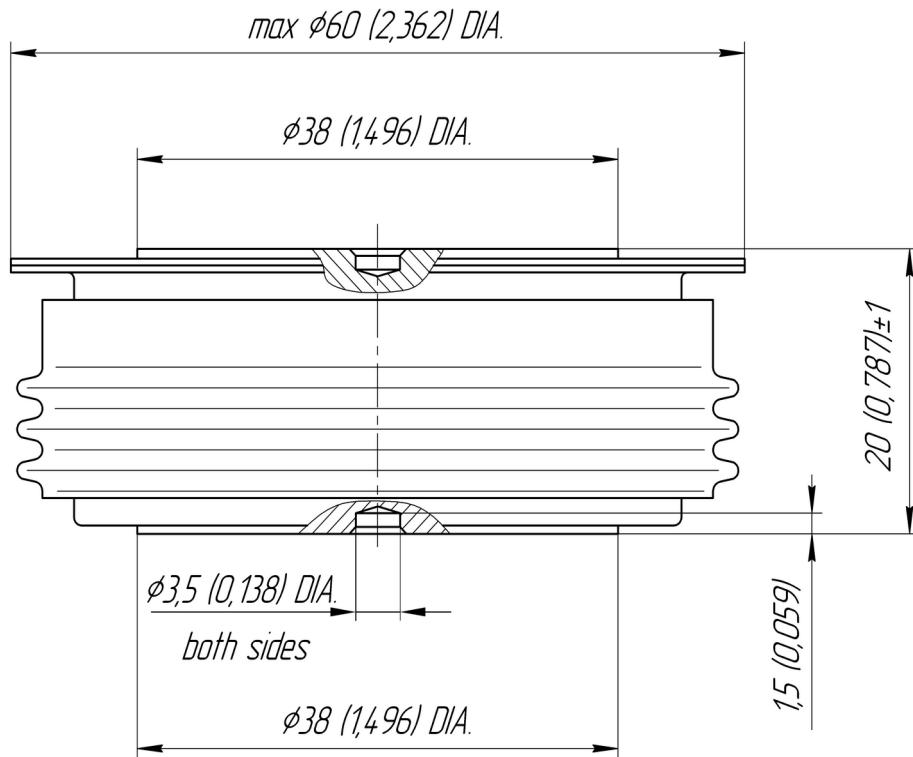
CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	2.00	T _j =25 °C; I _{FM} =1978 A
V _{F(TO)}	Forward threshold voltage, max	V	1.034	T _j =T _j max;
r _T	Forward slope resistance, max	mΩ	0.568	0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	70	T _j =T _j max; V _R =V _{RRM}
SWITCHING				
Q _{rr}	Total recovered charge, max	μC	3390	T _j =T _j max; I _{TM} =630 A;
t _{rr}	Reverse recovery time, max	μs	60	di _R /dt=-5 A/μs;
I _{rr}	Reverse recovery current, max	A	113	V _R =100 V
THERMAL				
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.027	Double side cooled
R _{thjc-A}			0.060	
R _{thjc-K}			0.049	
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.006	Direct current
MECHANICAL				
m	Weight, max	g	260	
D _s	Surface creepage distance	mm (inch)	23.69 (0.933)	
D _a	Air strike distance	mm (inch)	19.10 (0.752)	

PART NUMBERING GUIDE

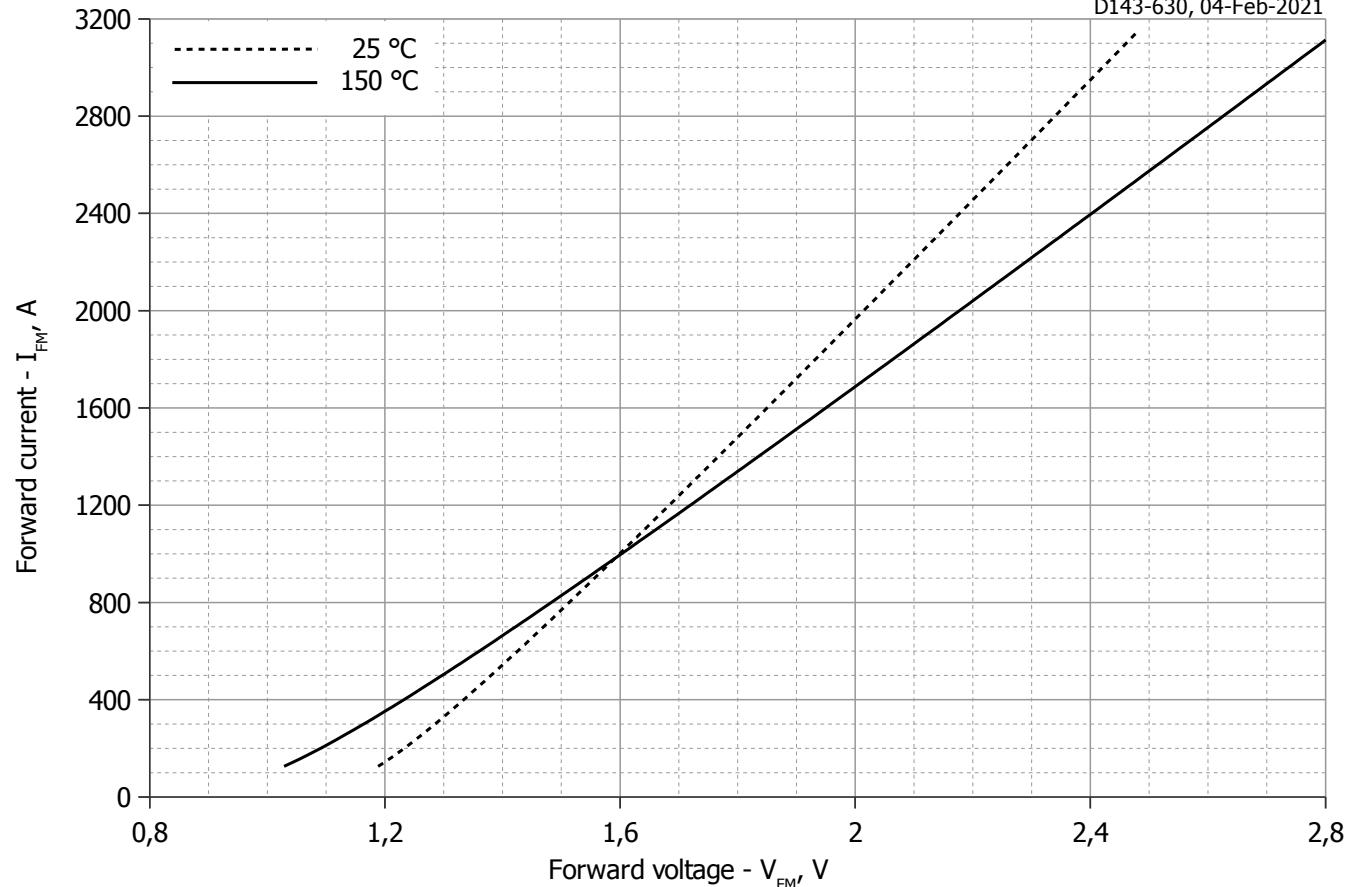
D	143	630	40	N
1	2	3	4	5

1. D — Rectifier Diode
2. Design version
3. Average forward current, A
4. Voltage code
5. Ambient conditions: N – normal; T – tropical

OVERALL DIMENSIONS**Package type: D.C2**

All dimensions in millimeters (inches)

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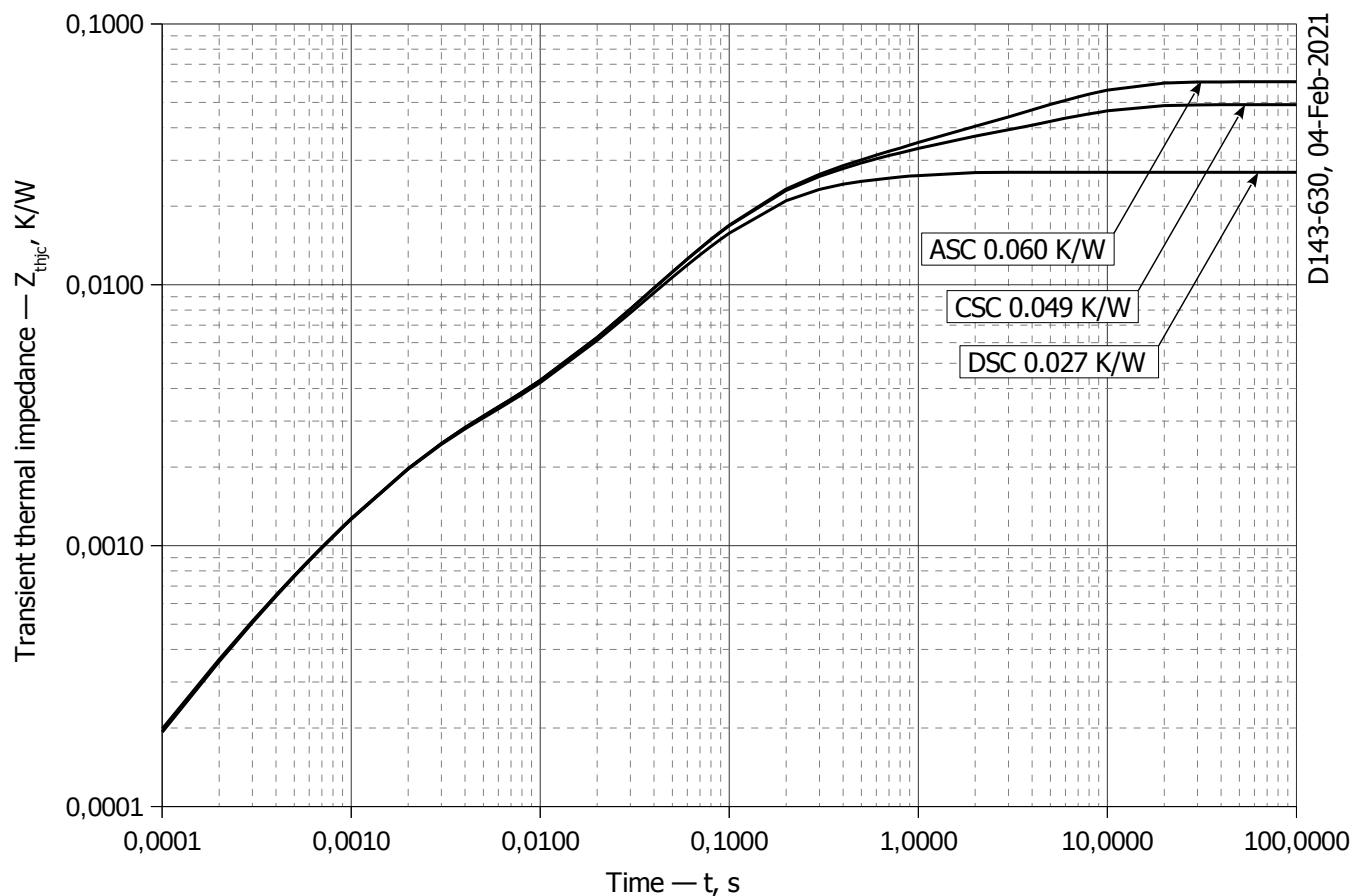
**Fig 1 – Forward characteristics of Limit device**

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j,\max}$
A	0.97410112	0.74306432
B	0.00039561	0.00053302
C	0.03475973	0.04287475
D	-0.00034032	0.00094230

Forward characteristic model (see Fig. 1).

**Fig 2 – Transient thermal impedance Z_{thjc} vs. time t**

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i , K/W	0.00000562	0.00531	0.01922	0.0004148	0.0019	0.000152
τ_i , s	7.79	0.5094	0.09719	0.01725	0.0016	0.0002257

DC Cathode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.017	0.001472	0.01786	0.00193	0.000193	0.0105
τ_i , s	5.328	0.1832	0.09031	0.001714	0.0002598	0.525

DC Anode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.0277	0.008681	0.01867	0.00196	0.000179	0.00277
τ_i , s	5.351	0.4584	0.09325	0.001734	0.0002174	0.9059

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

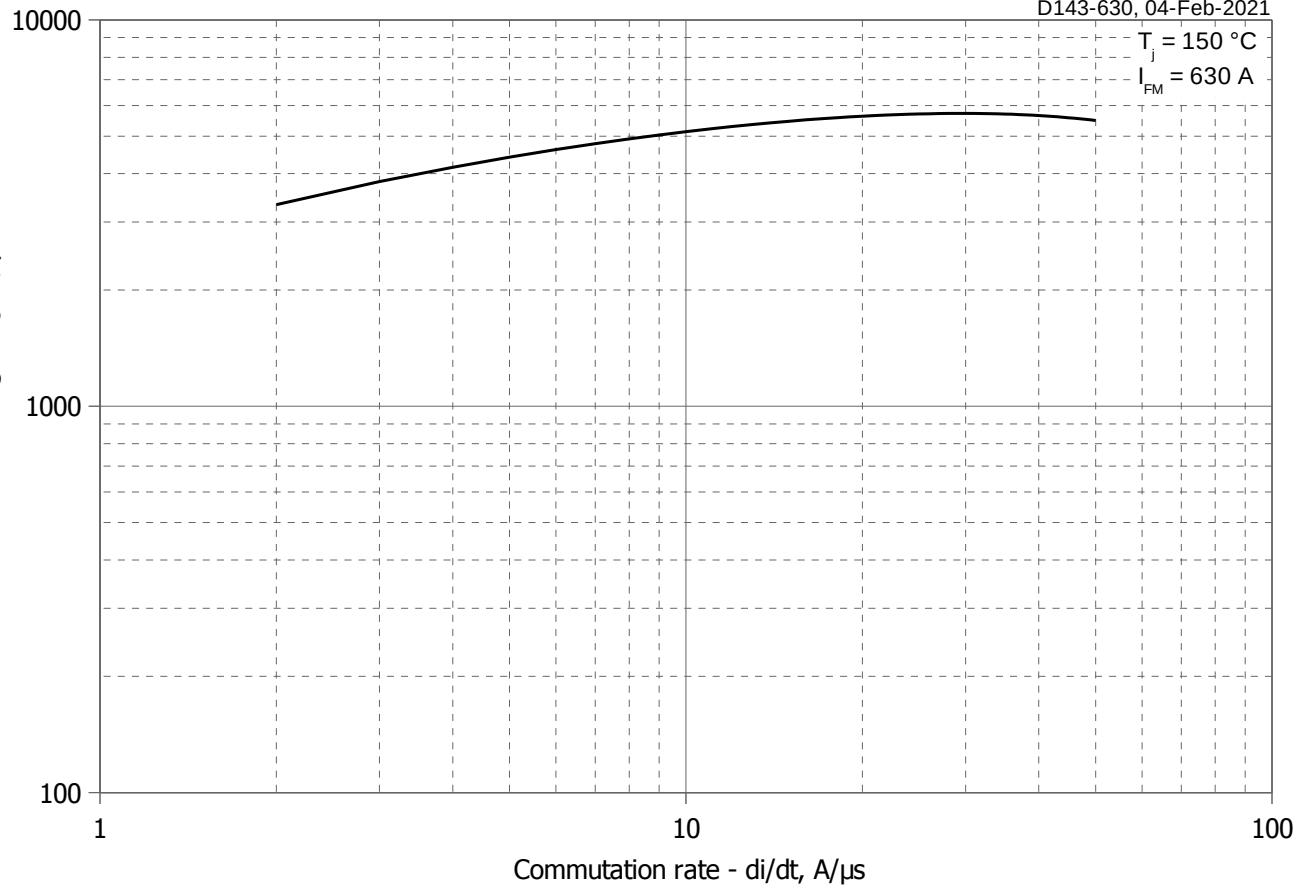


Fig 3 - Total recovered charge Q_{rr-i} (integral) vs. commutation rate di_R/dt

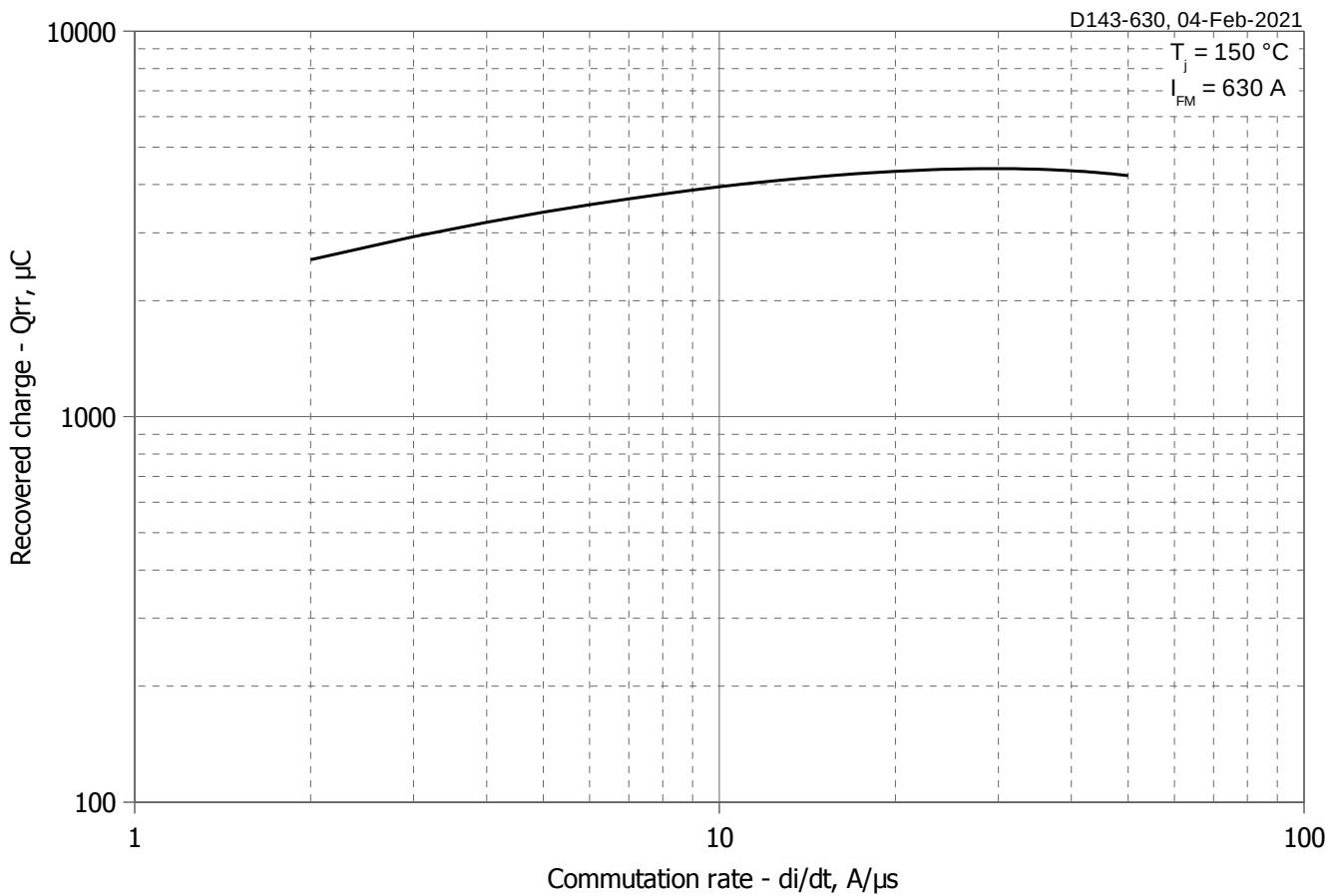


Fig 4 - Maximum recovered charge Q_{rr} vs. commutation rate di_R/dt (25% chord)

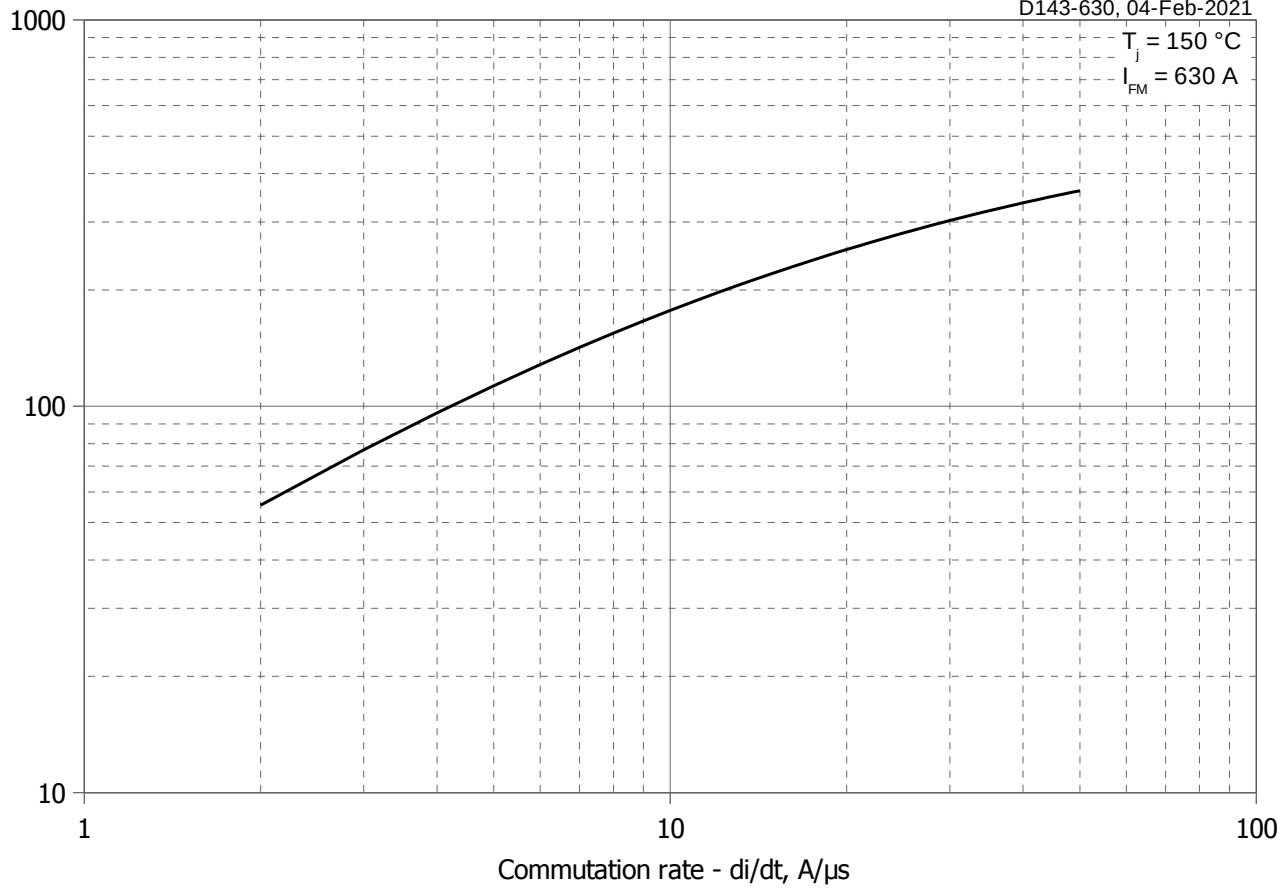


Fig 5 - Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

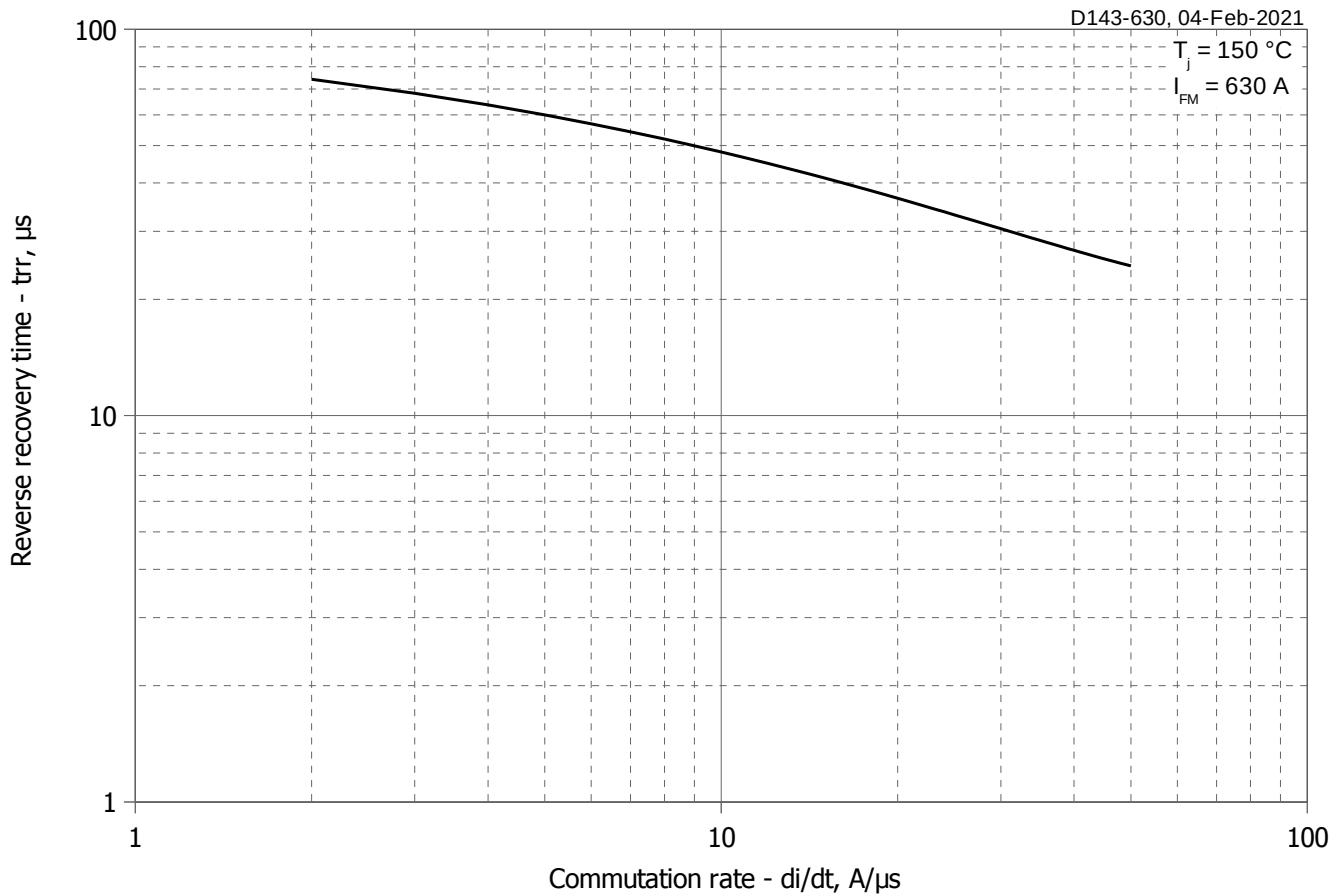


Fig 6 - Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

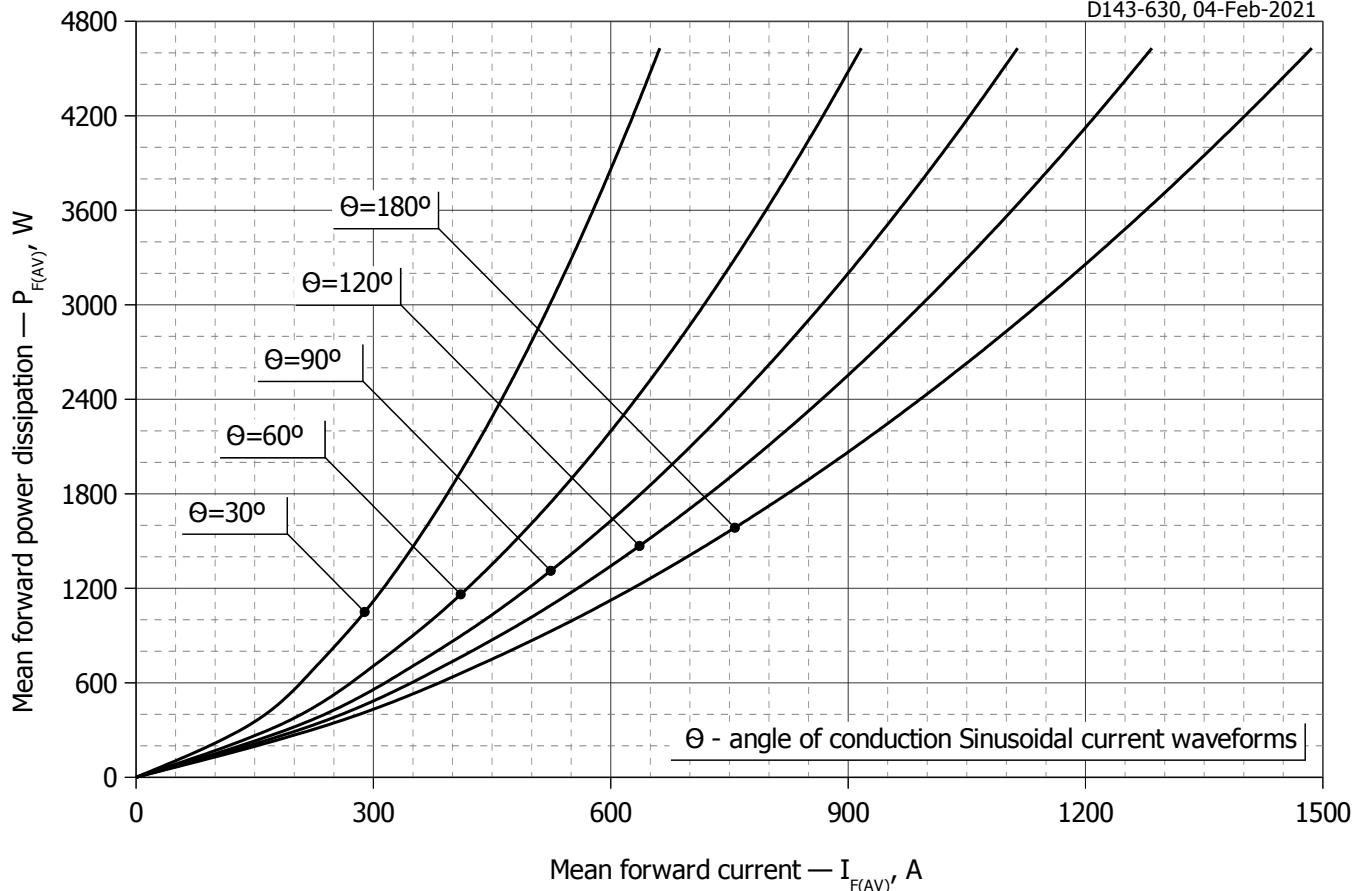


Fig. 7 - Mean forward power dissipation $P_{FA(V)}$ vs. mean forward current $I_{FA(V)}$ for sinusoidal current waveforms at different conduction angles (f=50Hz, DSC)

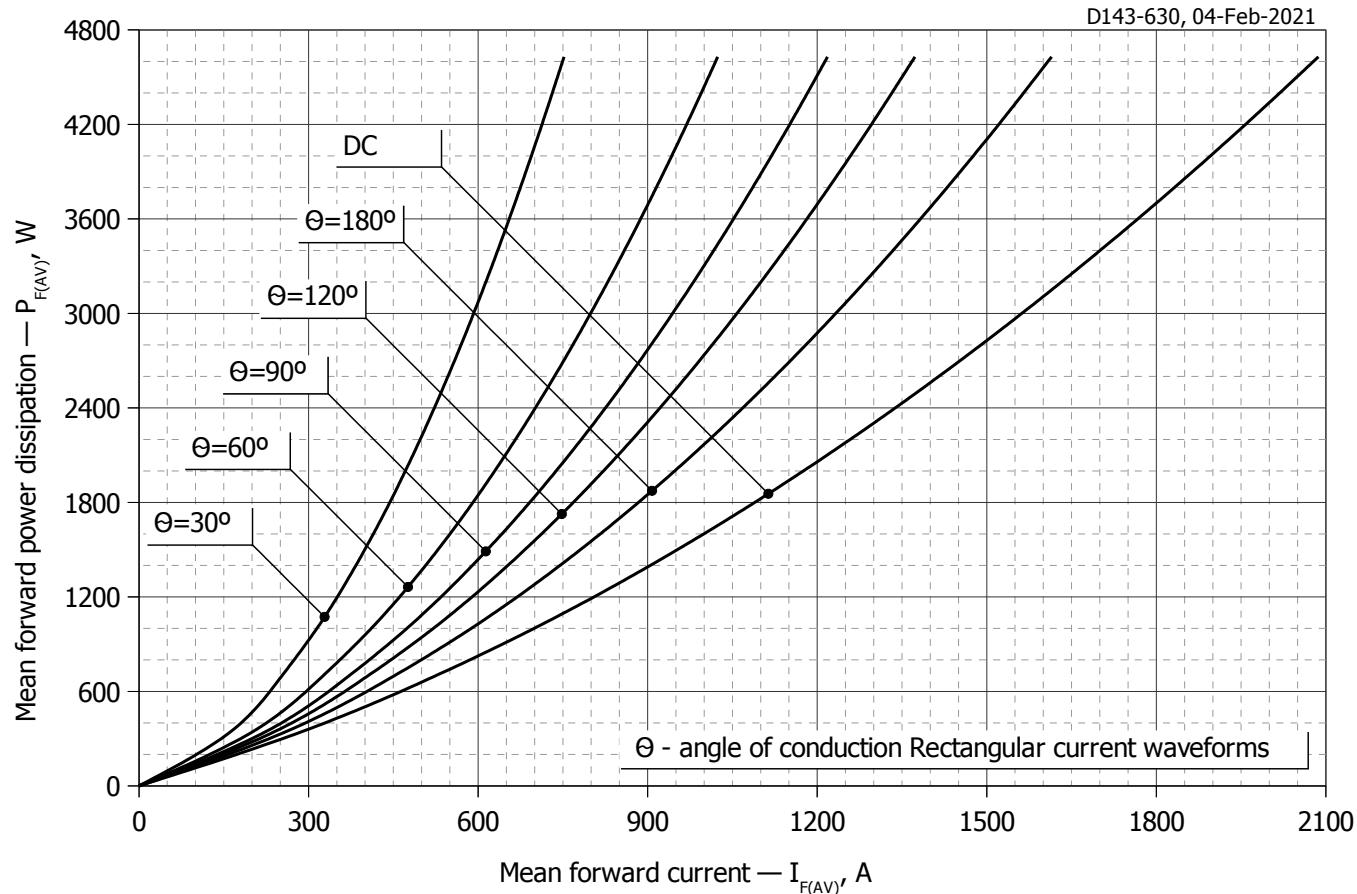


Fig. 8 – Mean forward power dissipation $P_{FA(V)}$ vs. mean forward current $I_{FA(V)}$ for rectangular current waveforms at different conduction angles and for DC (f=50Hz, DSC)

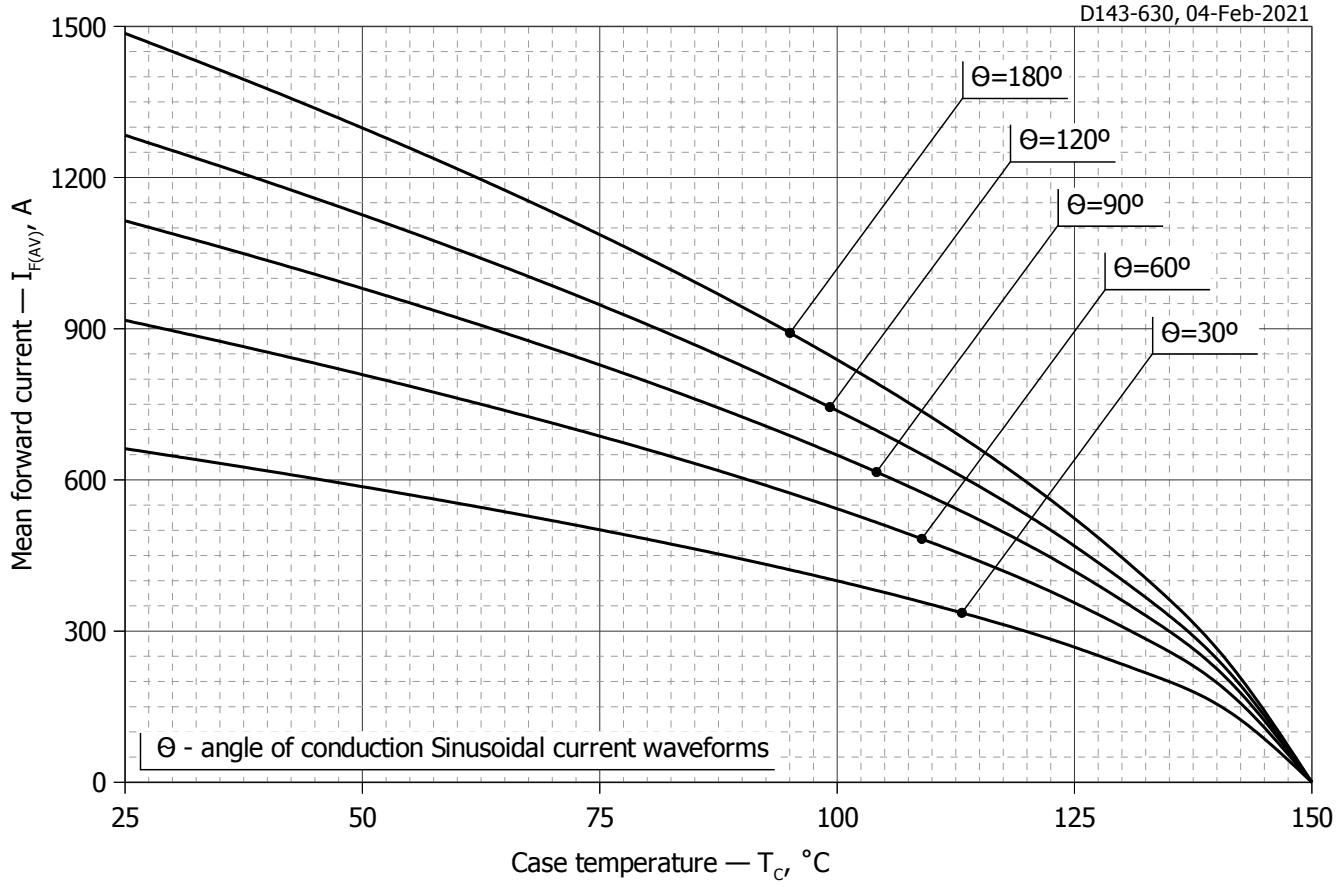


Fig. 9 – Mean forward current I_{FAV} vs. case temperature T_c for sinusoidal current waveforms at different conduction angles (f=50Hz, DSC)

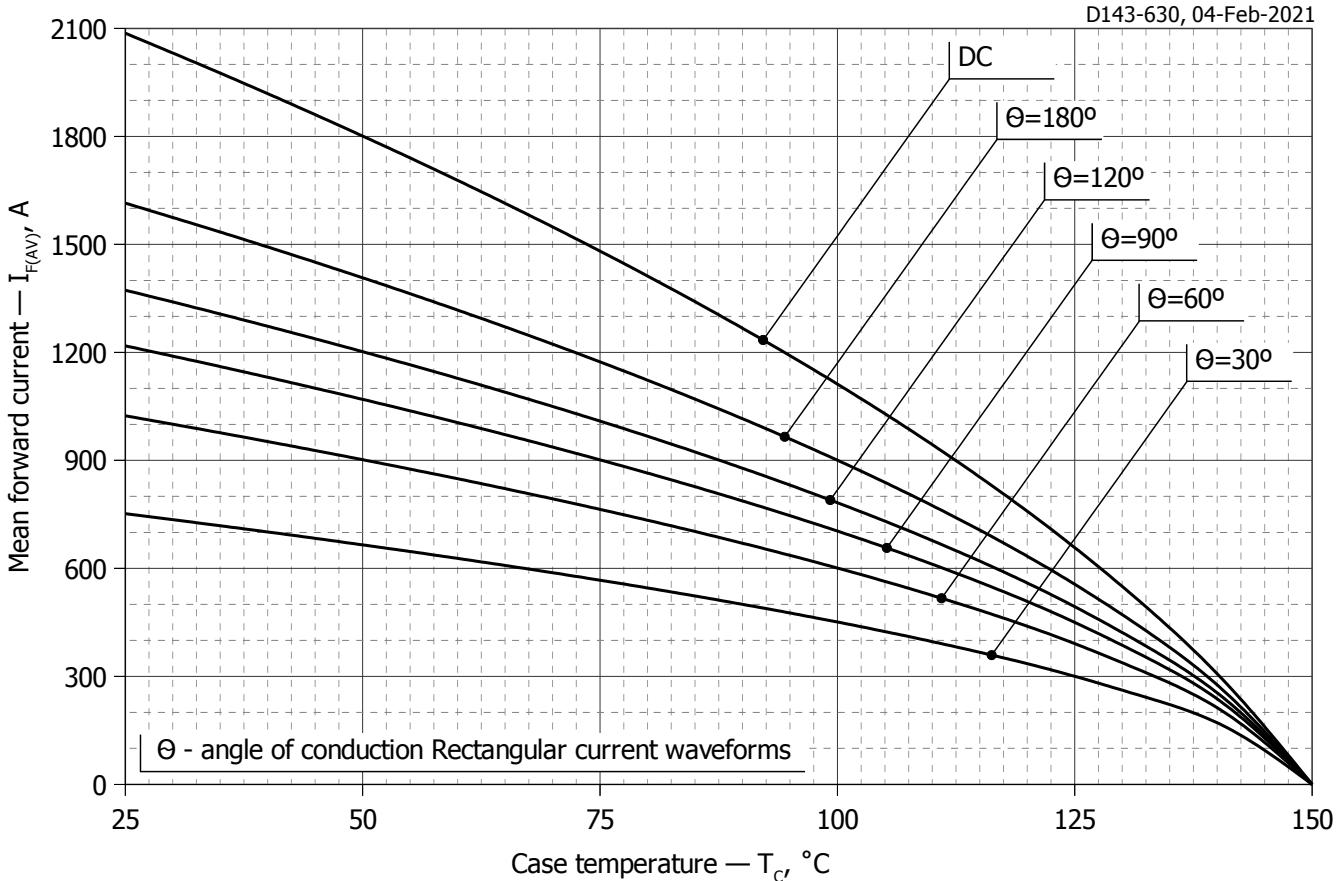


Fig. 10 - Mean forward current I_{FAV} vs. case temperature T_c for rectangular current waveforms at different conduction angles and for DC (f=50Hz, DSC)

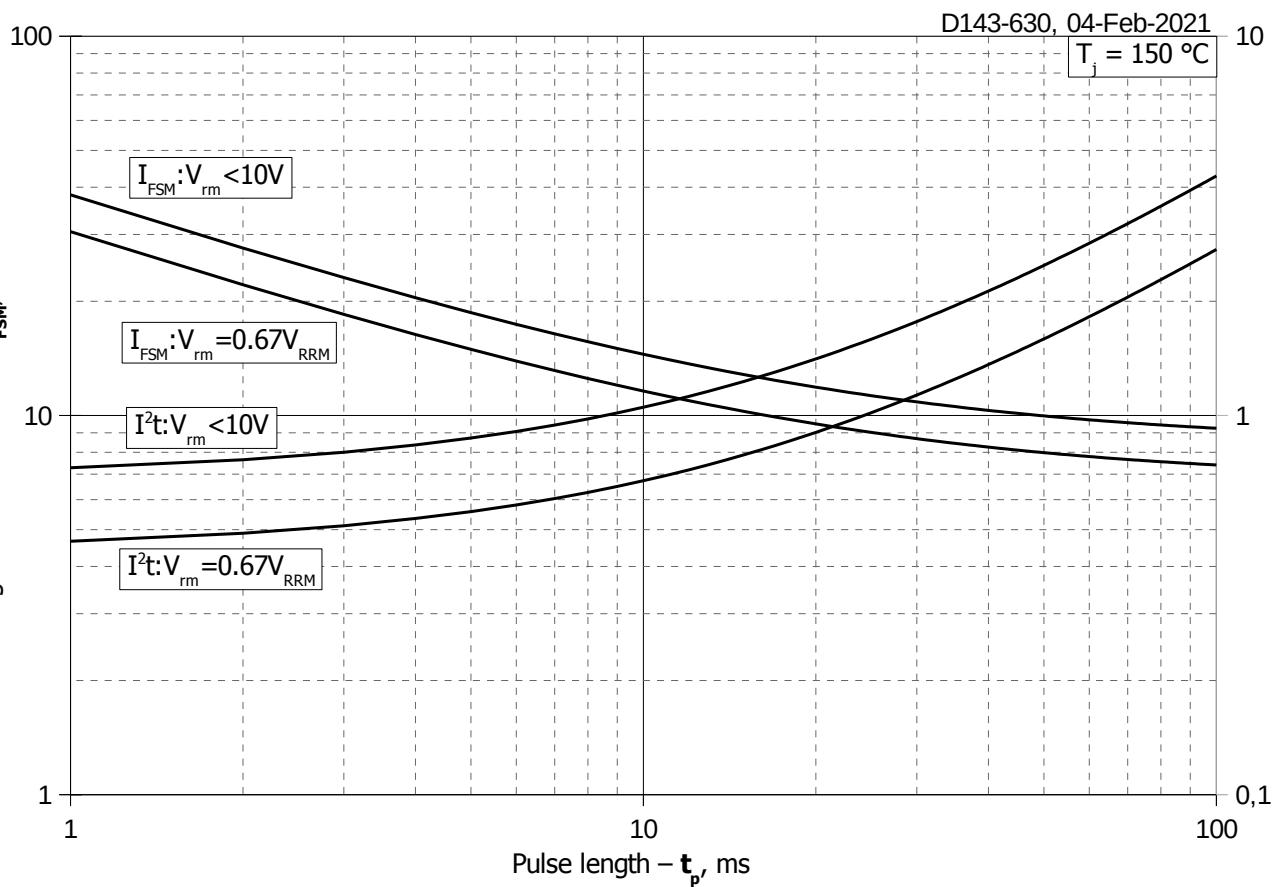


Fig. 11 – Maximum surge forward current I_{FSM} and safety factor I^2t vs. pulse length t_p

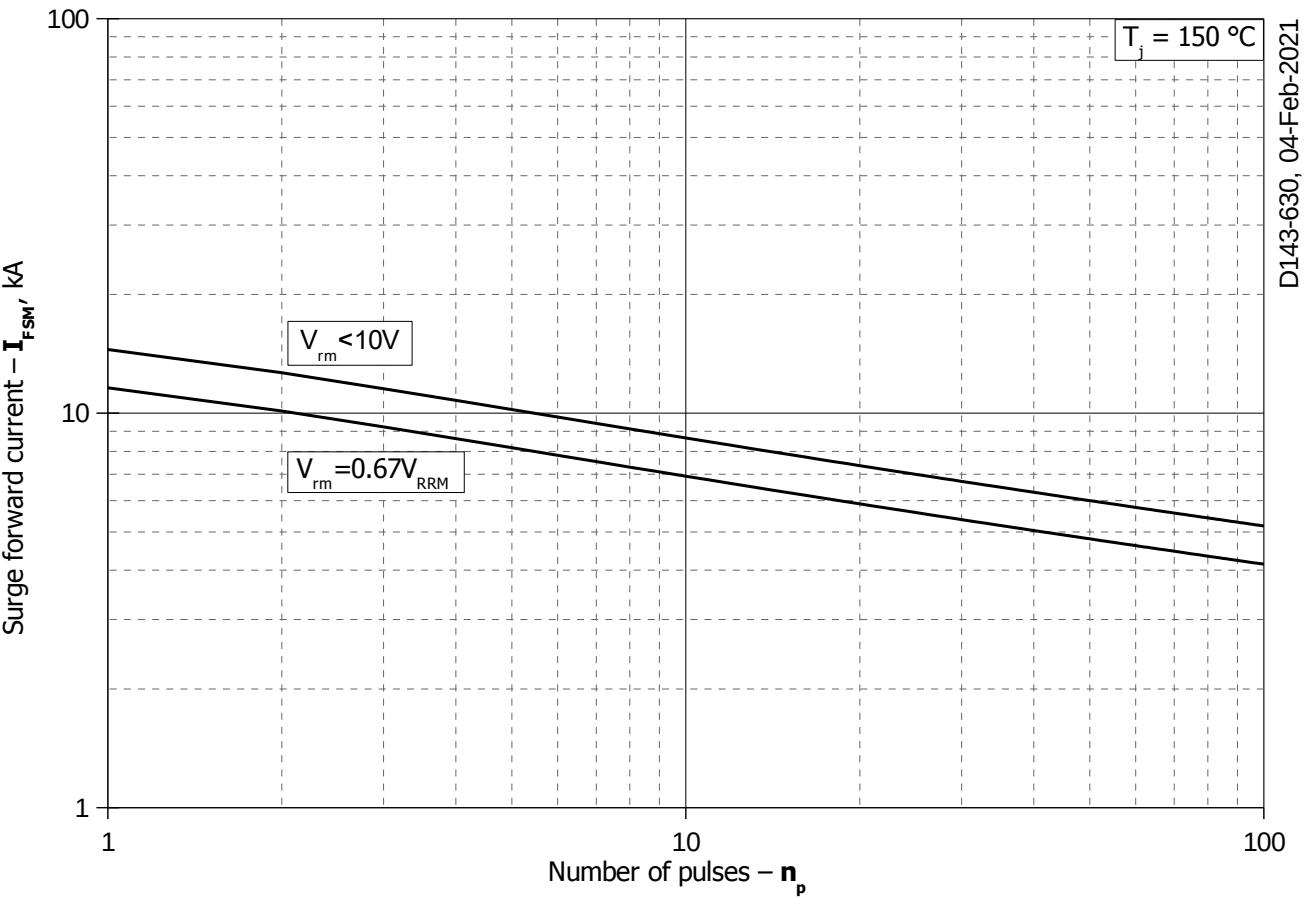


Fig. 12 - Maximum surge forward current I_{FSM} vs. number of pulses n_p